

METHOD OF REDUCING PLASMA CHARGE DAMAGE FOR PLASMA PROCESSES

ABSTRACT OF THE DISCLOSURE

A method is provided for depositing a thin film on a substrate in a process chamber with reduced incidence of plasma charge damage. A process gas containing a precursor gases suitable for forming a plasma is flowed into a process chamber, and a plasma is generated from the process gas to deposit the thin film on the substrate. The precursor gases are flowed into the process chamber such that the thin film is deposited at the center of the substrate more rapidly than at an edge of the substrate.

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